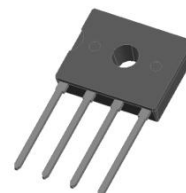
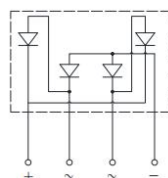


Bridge Rectifier Diode 整流桥

■ Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Ideal for PCB 适用于印刷电路板
Solder dip 275°C 7S 焊接 275 度 7 秒内
Package 封装: GBU



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	GBU8005	GBU801	GBU802	GBU804	GBU806	GBU808	GBU810	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
Forward Rectified Current 正向整流电流	I_F	8 (With Heat sink 带散热)							A
Forward Rectified Current 正向整流电流	I_F	3.2 (Without Heat sink 不带散热)							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	175							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	25							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^{\circ}\text{C}$, -55to+150 $^{\circ}\text{C}$							

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F		1.0		V	$I_F=4\text{A}$
Reverse Current 反向电流	I_R			5	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		25		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

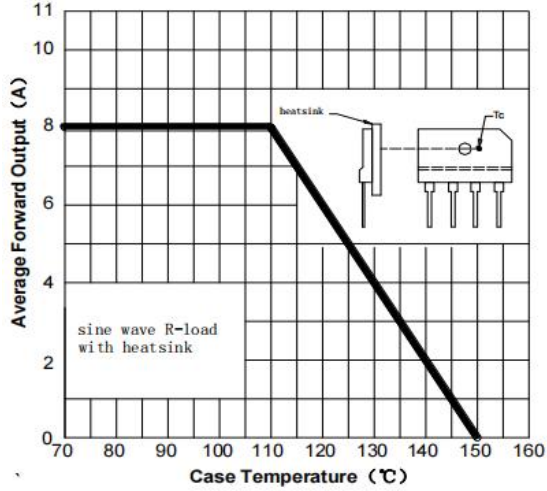


Figure 1: Forward Current Derating Curve

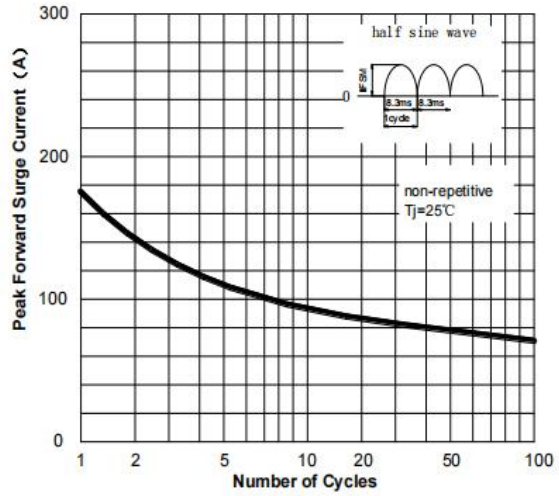


Figure 2: Peak Forward Surge Current

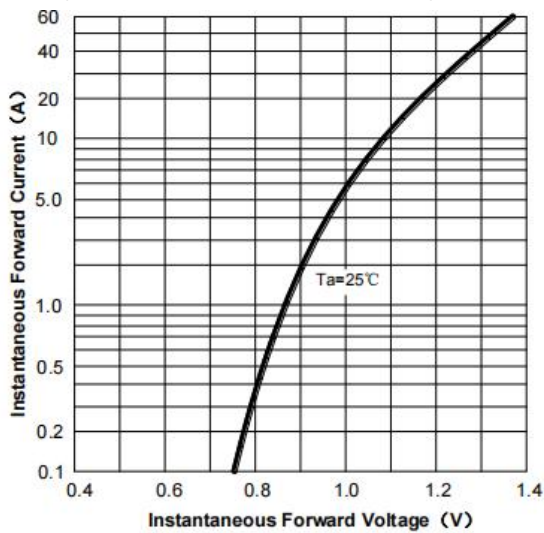


Figure 3: Instantaneous Forward Characteristics

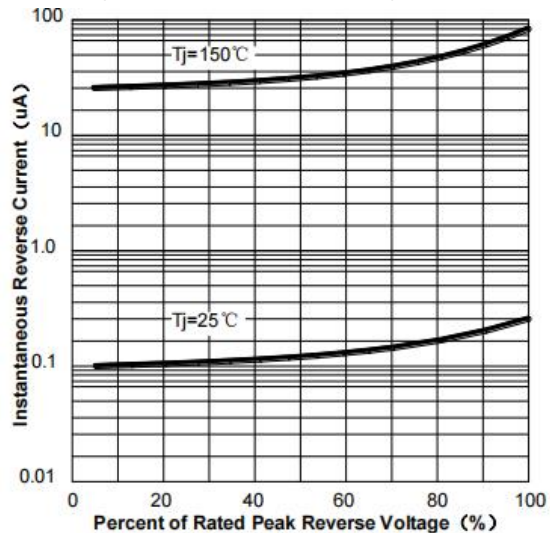
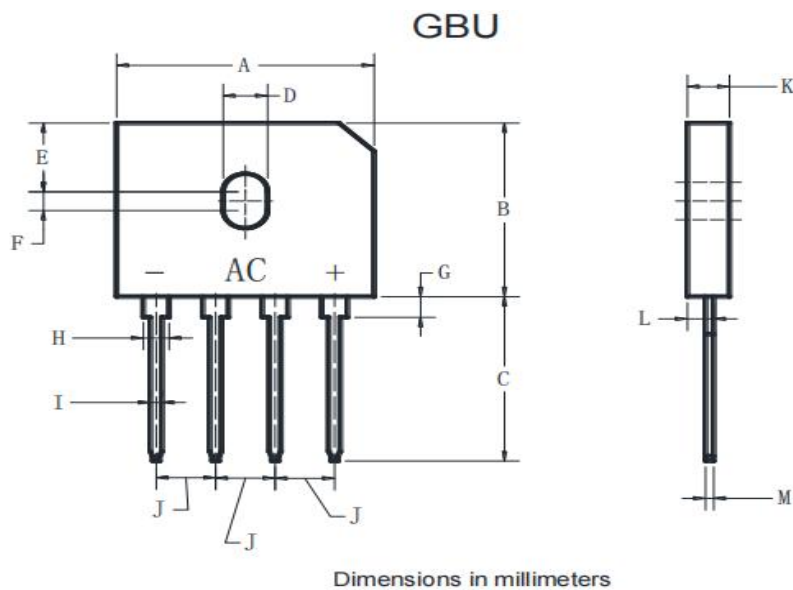


Figure 4: Reverse Leakage Characteristics

■Dimension 外形封装尺寸



GBU		
Dim	Min	Max
A	21.80	22.30
B	18.30	18.80
C	17.50	18.00
D	3.50	4.10
E	7.40	7.90
F	1.65	2.16
G	1.91	2.54
H	2.06	2.54
I	1.02	1.27
J	4.83	5.33
K	3.30	3.56
L	2.40	2.66
M	0.46	0.56